

Search History. 12/11/04. *[Signature]* (2 pp.)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5	"825543".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/12 19:51
L2	120	channel adj width near12 performance and (mosfet transistor field adj effect adj transistor).ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/12 19:52
L3	14	channel adj width near12 performance.ti,ab,clm. and (mosfet transistor field adj effect adj transistor).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/12 19:55
L4	1	jp-11330465\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/12 19:57
L5	280	width near4 channel near4 increas\$3.ti,ab,clm. and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/12 19:58
L6	6	(US-20040222473-\$ or US-20040222477-\$ or US-20020089019-\$ or US-20020003257-\$).did. or (US-6436798-\$).did. or (JP-11330465-\$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2004/12/12 20:49
L7	2	6 and deplet\$3	US-PGPUB; USPAT; DERWENT	OR	OFF	2004/12/12 21:07
L8	11	advantage near4 depletion adj mode and mosfet	US-PGPUB; USPAT; DERWENT	OR	OFF	2004/12/12 21:30
L9	2	low near6 voltage near6 logic and high near4.voltage near4 MOSFET and short adj channel adj effect	US-PGPUB; USPAT; DERWENT	OR	OFF	2004/12/12 21:34
L10	203	low near6 voltage near6 logic and high near4 voltage near4 MOSFET	US-PGPUB; USPAT; DERWENT	OR	OFF	2004/12/12 22:18
L11	3583	((257/288) or (257/327) or (257/331) or (257/332) or (257/335) or (257/365) or (257/368) or (257/499) or (257/500)).CCLS.	US-PGPUB; USPAT	OR	OFF	2004/12/12 22:20

L12	27	11 and channel near4 width and (hot adj electron short adj channel) and ("high" near3 voltage high-voltage) near22 ("low" near3 voltage low-voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/12 22:21
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